

TECHNICAL SPECIFICATION



Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection – Glossary –

Part 4-4: Piezoelectric materials – ~~Materials~~ Single crystal wafers for surface acoustic wave (SAW) devices



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INTERNATIONAL
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CONTENTS

FOREWORD.....	3
1 Scope.....	5
2 Normative references	5
3 Terms and definitions	5
3.1 Single crystals for SAW wafer	5
3.2 Terms and definitions related to LN and LT crystals	6
3.3 Terms and definitions related to all crystals	7
3.4 Flatness.....	7
3.5 Definitions of appearance defects	11
3.6 Other terms and definitions	12
Bibliography.....	14
Figure 1 – Example of site distribution for LTV measurement All sites have their centres within the FQA	8
Figure 2 – LTV is a positive number and is measured at value of each site	8
Figure 3 – Schematic diagram of Sori	9
Figure 4 – Wafer indication sketch and measurement points for TV5 determination	10
Figure 5 – Schematic diagram of TTV	10
Figure 6 – Schematic diagram of warp	10
Table 1 – Description of wafer orientations	12

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

PIEZOELECTRIC, DIELECTRIC AND ELECTROSTATIC DEVICES AND ASSOCIATED MATERIALS FOR FREQUENCY CONTROL, SELECTION AND DETECTION – GLOSSARY –

Part 4-4: Piezoelectric materials – ~~Materials~~ Single crystal wafers for surface acoustic wave (SAW) devices

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Technical specifications are subject to review within three years of publication to decide whether they can be transformed into International Standards.

IEC TS 61944-4-4, which is a technical specification, has been prepared by IEC technical committee 49: Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection.

This third edition of IEC 61994-4-4 cancels and replaces the second edition published in 2010. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

- a) the new terms and definitions given in IEC 62276:2016 have been taken into account;
- b) the general title has been changed according to the change in the title of TC 49 in 2009.
- c) the part title has been changed according to the title of IEC 62276:2016.

The text of this technical specification is based on the following documents:

Enquiry draft	Report on voting
49/1283/DTS	49/1287/RVC

Full information on the voting for the approval of this technical specification can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 61994 series, published under the general title *Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection – Glossary*, can be found on the IEC website.

Future standards in this series will carry the new general title as cited above. Titles of existing standards in this series will be updated at the time of the next edition.

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Part 4-4: Piezoelectric materials – ~~Materials~~ Single crystal wafers for surface acoustic wave (SAW) devices

1 Scope

This part of IEC 61994 ~~specifies~~ gives the terms and definition for single crystal wafers ~~applied~~ for surface acoustic wave (SAW) devices representing the state of the art, ~~which are intended for use in the standards and documents of IEC technical committee 49.~~

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

~~ISO 4287, Geometrical Product Specifications (GPS) – Surface texture: Profile method – Terms, definitions and surface texture parameters~~

There are no normative references in this document.

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia, available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

~~3.1 acceptable quality level~~

~~AQL~~

~~AQL is the maximum percent defective (or the maximum number of defects per hundred units) that, for purposes of sampling inspections, can be considered satisfactory as a process average~~

~~[IEC 60410:1973, 4.2]~~

3.1 Single crystals for SAW wafer

3.1.1

as-grown synthetic quartz crystal

right-handed or left-handed single crystal quartz grown hydrothermally. ~~“As-grown” refers to the state of processing and indicates a state prior to mechanical fabrication~~

[SOURCE: ~~IEC 61994-4-1:2007, 3.4~~ IEC 62276:2016, 3.1.1, modified – Notes 1 and 2 to entry have been removed.]

3.1.2

lanthanum gallium silicate

LGS

single crystals described by the chemical formula to $\text{La}_3\text{Ga}_5\text{SiO}_{14}$, grown by Czochralski (crystal pulling from melt) or other growing methods

[SOURCE: IEC 62276:2005 2016, 3.1.5]

3.1.3

lithium niobate

LN

single crystals approximately described by chemical formula LiNbO_3 , grown by Czochralski (crystal pulling from melt) or other growing methods

[SOURCE: IEC 62276:2005 2016, 3.1.2]

3.1.4

lithium tantalate

LT

single crystals approximately described by chemical formula LiTaO_3 , grown by Czochralski (crystal pulling from melt) or other growing methods

[SOURCE: IEC 62276:2005 2016, 3.1.3]

3.1.5

lithium tetraborate

LBO

single crystals described by the chemical formula to $\text{Li}_2\text{B}_4\text{O}_7$, grown by Czochralski (crystal pulling from melt), vertical Bridgman, or other growing methods

[SOURCE: IEC 62276:2005 2016, 3.1.4]

3.2 Terms and definitions related to LN and LT crystals

3.2.1

curie temperature

T_c

phase transition temperature between ferroelectric and paraelectric phases measured by differential thermal analysis (DTA) or dielectric measurement

[SOURCE: IEC 62276:2005 2016, ~~3.3.1~~ 3.2.1]

3.2.2

polarization ~~(or poling)~~ process

electrical process used to establish a single domain crystal

[SOURCE: IEC 62276:2005 2016, ~~3.3.3~~ 3.2.3]

3.2.3

reduction process

REDOX reaction to increase conductivity to reduce the harmful effects of pyroelectricity

[SOURCE: IEC 62276:2005 2016, ~~3.3.4~~ 3.2.4]

3.2.4

reduced LN

LN treated with a reduction process, ~~sometimes referred to as “black LN”~~

[SOURCE: IEC 62276:2005 2016, ~~3.3.4.1~~ 3.2.5, modified – Note 1 to entry has been removed.]

3.2.5

reduced LT

LT treated with a reduction process, ~~sometimes referred to as “black LT”~~

[SOURCE: IEC 62276:2005 2016, ~~3.3.4.2~~ 3.2.6, modified – Note 1 to entry has been removed.]

3.2.6

single domain

ferroelectric crystal with uniform electrical polarization throughout (for LN and LT)

[SOURCE: IEC 62276:2005 2016, ~~3.3.2~~ 3.2.2]

3.3 Terms and definitions related to all crystals

3.3.1

congruent composition

chemical composition of a single crystal in a thermodynamic equilibrium with a molten solution of the same composition during the growth process

[SOURCE: IEC 62276:2005 2016, ~~3.4.2~~ 3.3.2]

3.3.2

lattice constant

length of ~~one~~ unit cell along a major crystallographic axis measured by X-ray using the Bond method

[SOURCE: IEC 62276:2005 2016, ~~3.4.1~~ 3.3.1]

3.3.3

twin

~~crystallographic defect occurring in a single crystal~~

~~NOTE The twin is separated from the rest of the material by a boundary, generally aligned along a crystal plane. The lattices on either side of the boundary are crystallographic mirror images of one another.~~

two or more same single crystals which are combined together by the law of symmetrical plane or axis

[SOURCE: IEC 62276:2005 2016, ~~3.4.3~~ 3.3.3, modified – Notes 1 and 2 to entry have been removed.]

3.4 Flatness

3.4.1

fixed quality area

FQA

central area of a wafer surface, defined by a nominal edge exclusion, X, over which the specified values of a parameter apply

[SOURCE: IEC 62276:2005 2016, ~~3.7.1~~ 3.4.1, modified – Note 1 to entry has been removed.]

3.4.2 local thickness variation LTV

variation determined by a measurement of a matrix of sites with defined edge dimensions (e.g. 5 mm × 5 mm).

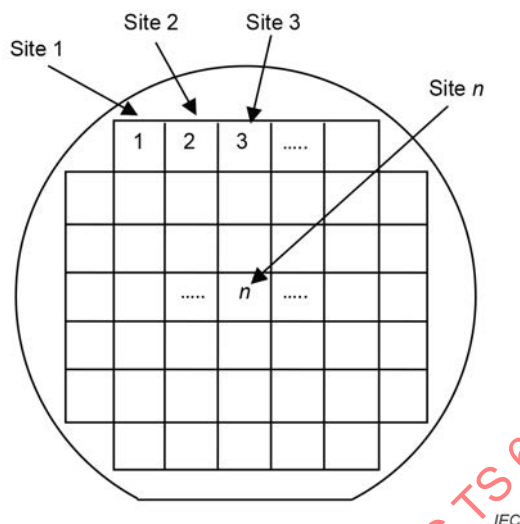


Figure 1 – Example of site distribution for LTV measurement
All sites have their centres within the FQA

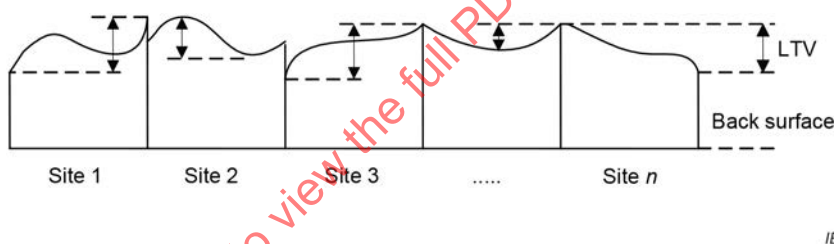


Figure 2 – LTV is a positive number and is measured at value of each site

Note 1 to entry: All sites have their centres within the FQA.

Note 2 to entry: Measurement is performed on a clamped wafer with the reference plane as defined in 3.30a 3.4.5 a). A site map example is shown in Figure 1. The value is always a positive number and is defined for each site as the difference between the highest and lowest points within each site, as shown in Figure 2. For a wafer to meet an LTV specification, all sites must shall have LTV values less than the specified value.

[SOURCE: IEC 62276:2005 2016, 3.7.8 3.4.8]

3.4.3 focal plane deviation FPD

deviation measured relative to the 3-point reference plane

Note 1 to entry: The 3-point reference plane is defined in 3.30 b 3.4.5 b).

Note 2 to entry: The value obtained indicates the maximum distance between a point on the wafer surface (within the FQA) and the focal plane. If that point is above the reference, the FPD is positive. If that point is below the reference plane, the FPD is negative.

[SOURCE: IEC 62276:2005 2016, 3.7.10 3.4.10]

3.4.4 percent local thickness variation

PLTV

percentage of sites that fall within the specified values for LTV

Note 1 to entry: As with the LTV measurement, this is a clamped measurement.

[SOURCE: IEC 62276:2005 2016, ~~3.7.9~~ 3.4.9]

3.4.5 reference plane

~~depends~~ plane depending on the flatness measurement and ~~needs to be specified. It~~ which can be any of the following:

- for clamped measurements, the flat chuck surface that contacts the back surface of the wafer;
- for without clamped measurements, three points at specified locations on the front surface within the FQA;
- for without clamped measurements, the least-squares fit to the front surface using all measured points within the FQA

~~d) the least squares fit to the front surface using all measured points within one site~~

[SOURCE: IEC 62276:2005 2016, ~~3.7.2~~ 3.4.2]

3.4.6

site

square area on the front surface of the wafer with one side parallel to the OF

Note 1 to entry: Flatness parameters are assessed either globally for the FQA, or for each site individually.

[SOURCE: IEC 62276:2005 2016, ~~3.7.3~~ 3.4.3]

3.4.7

Sori

~~sori describes the deformation of an unclamped wafer and is defined as the~~ maximum difference between a point on the front surface and a reference plane

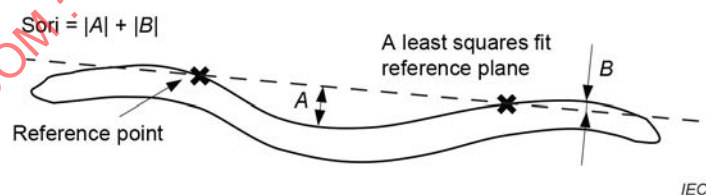


Figure 3 – Schematic diagram of Sori

Note 1 to entry: Sori describes the deformation of an unclamped wafer, as shown in Figure 3.

Note 2 to entry: In contrast to warp, in this case the reference plane is defined by a least-squares fit to the front surface (3.4.5 c)).

[SOURCE: IEC 62276:2005 2016, ~~3.7.7~~ 3.4.7]

3.4.8

thickness variation for five points

TV5

measure of wafer thickness variation defined as the maximum difference between five thickness measurements

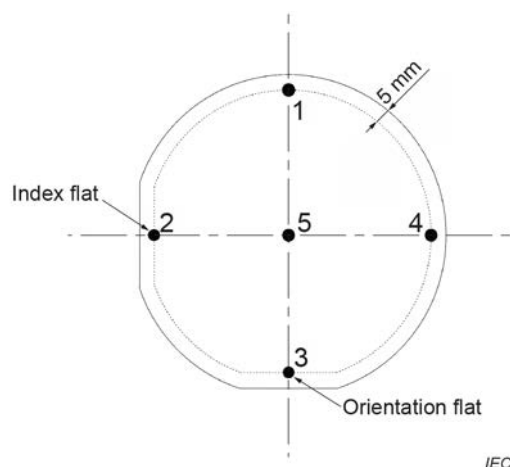


Figure 4 – Wafer indication sketch and measurement points for TV5 determination

Note 1 to entry: Thickness is measured at the centre of the wafer and at four peripheral points shown in Figure 4.

[SOURCE: IEC 62276:2005 2016, 3.7.4 3.4.4]

3.4.9

total thickness variation

TTV

difference between the maximum thickness (A) and the minimum thickness (B) as shown in Figure 4.

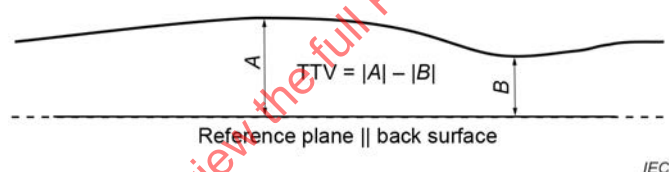


Figure 5 – Schematic diagram of TTV

Note 1 to entry: The maximum thickness is represented by the letter A and the minimum thickness is represented by the letter B in Figure 5.

Note 2 to entry: Measurement of TTV is performed under clamped conditions with the reference plane as defined in 3.30a) 3.4.5 a).

[SOURCE: IEC 62276:2005 2016, 3.7.5 3.4.5]

3.4.10

warp

warp describes the deformation of an unclamped wafer and is defined as the maximum difference between a point on the front surface and a reference plane

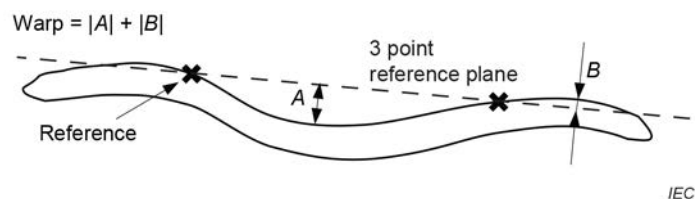


Figure 6 – Schematic diagram of warp

Note 1 to entry: Warp (shown in Figure 6) describes the deformation of an unclamped wafer.

Note 2 to entry: The reference plane is defined by 3-points as described in ~~3.30b~~ 3.4.5 b). Warp is a bulk property of a wafer and not of the exposed surface alone.

[SOURCE: IEC 62276:2005 2016, ~~3.7.6~~ 3.4.6]

3.5 Definitions of appearance defects

3.5.1

chip

region where material has been removed from the surface or edge of the wafer

Note 1 to entry: The size can be expressed by its maximum radial depth and peripheral chord length.

[SOURCE: IEC 62276:2005 2016, ~~3.16.4~~ 3.5.4]

3.5.2

contamination

~~the first is defined as area and the second as particulate. The first is caused by surface contaminants that cannot be removed by cleaning or are stained after cleaning. Those may be foreign matter on the surface of, for example a localized area that is smudged, stained, discoloured, mottled, etc., or large areas exhibiting a hazy or cloudy appearance resulting from a film of foreign materials~~

foreign matter on a surface of wafer which cannot be removed after cleaning

[SOURCE: IEC 62276:2005 2016, ~~3.16.1~~ 3.5.1]

3.5.3

crack

fracture that extends to the surface and may or may not penetrate the entire thickness of the wafer

[SOURCE: IEC 62276:2005 2016, ~~3.16.2~~ 3.5.2]

3.5.4

dimple

smooth surface depression larger than 3 mm in diameter

[SOURCE: IEC 62276:2005 2016, ~~3.16.5~~ 3.5.5]

3.5.5

orange peel

large featured, roughened surface visible to the unaided eye under diffuse illumination

Note 1 to entry: This is also called pear skin.

[SOURCE: IEC 62276:2005 2016, ~~3.16.7~~ 3.5.7]

3.5.6

pit

non-removable surface anomaly such as a hollow, typically resulting from a bulk defect or faulty manufacturing process

[SOURCE: IEC 62276:2005 2016, ~~3.16.6~~ 3.5.6, modified – The example has been included into the definition.]

3.5.7

scratch

shallow groove or cut below the established plane of the surface, with a length to width ratio greater than 5:1

[SOURCE: IEC 62276:2005 2016, ~~3.16.3~~ 3.5.3]

3.6 Other terms and definitions

3.6.1

back surface roughness

~~definitions of R_a are given in ISO 4287~~

roughness which scatters and suppresses bulk wave spurious at back surface

[SOURCE: IEC 62276:2005 2016, ~~3.8~~ 3.6.4]

3.6.2

bevel

slope or rounding of the wafer perimeter

Note 1 to entry: Bevel is also referred to as “edge profile”.

Note 2 to entry: The process of creating a bevel is called “bevelling” or “edge rounding”.

Note 3 to entry: The profile and its tolerances should be specified by the supplier.

[SOURCE: IEC 62276:2005 2016, ~~3.13~~ 3.6.9]

3.6.3

description of orientation and SAW propagation

indication of the surface orientation and the SAW propagation direction, separated by the symbol “-“

Note 1 to entry: Specification of a 0° orientation is normally omitted.

Note 2 to entry: Typical examples for these expressions are shown in Table 1.

Note 3 to entry: Description of wafer orientation rule is shown in Annex A of IEC 62276:2016.

Table 1 – Description of wafer orientations

Material LT Quartz	LN	LT	Quartz crystal	LBO	LGS
Expression	128° Y-X Y-Z 64° Y-X	X-112° Y 36° Y-X	ST-X	45° X-Z	yxlt/48,5°/26,6°

[SOURCE: IEC 62276:2005 2016, ~~3.10~~ 3.6.6]

3.6.4

diameter of wafer

diameter of circular portion of wafer excluding the OF and SF regions

[SOURCE: IEC 62276:2005 2016, ~~3.14~~ 3.6.10]

3.6.5

manufacturing lot

lot established by agreement between the customer and the supplier

[SOURCE: IEC 62276:2005 2016, ~~3.2~~ 3.6.1]

3.6.6

orientation flat

OF

flat portion of wafer perimeter indicating the crystal orientation. ~~Generally, the orientation flat corresponds to the SAW propagation direction. It is also referred to as the "primary flat" (see Figure 3)~~

[SOURCE: IEC 62276:2005 2016, ~~3.5~~ 3.6.2, modified – Notes 1 and 2 to entry have been removed.]

3.6.7

secondary flat

SF

flat portion of wafer perimeter shorter than the OF. ~~When present, the SF indicates wafer polarity and can serve to distinguish different wafer cuts. It is also referred to as the "sub-orientation flat" (see Figure 3)~~

[SOURCE: IEC 62276:2005 2016, 3.6.3, modified – Notes 1 and 2 to entry have been removed.]

3.6.8

ST-cut

~~although the original definition is 42,75 ° rotated Y-cut and X-propagation, the actual cut angle can range from 20 ° to 42,75 ° in order to achieve a zero temperature coefficient~~
cut direction of quartz to achieve zero temperature coefficient of frequency

[SOURCE: IEC 62276:2005 2016, ~~3.11~~ 3.6.7, modified – The words "of frequency" have been added at the end of the definition.]

3.6.9

surface orientation

crystallographic ~~at~~ orientation of the axis perpendicular to the polished surface of wafer

[SOURCE: IEC 62276:2005 2016, ~~3.9~~ 3.6.5]

3.6.10

tolerance of surface orientation

acceptable difference between specified surface orientation and measured orientation, measured by X-ray diffraction

[SOURCE: IEC 62276:2005 2016, ~~3.12~~ 3.6.8]

3.6.11

wafer thickness

thickness measured at the centre of the wafer

[SOURCE: IEC 62276:2005 2016, ~~3.15~~ 3.6.11]

Bibliography

~~IEC 60050-561:1991, International Electrotechnical Vocabulary (IEV) — Chapter 561: Piezo-electric devices for frequency control and selection — Amendment 1 (1995)~~
~~Amendment 2 (1997)~~

~~IEC 60410:1973, Sampling plans and procedures for inspection by attributes~~

~~IEC 61994-4-1:2007, Piezoelectric and dielectric devices for frequency control and selection — Glossary — Part 4-1: Piezoelectric materials — Synthetic quartz crystal~~

IEC 62276:2005 2016, Single crystal wafers for surface acoustic wave (SAW) device applications – Specifications and measuring methods

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CONTENTS

FOREWORD.....	3
1 Scope.....	5
2 Normative references	5
3 There are no normative references in this document.Terms and definitions	5
3.1 Single crystals for SAW wafer	5
3.2 Terms and definitions related to LN and LT crystals	6
3.3 Terms and definitions related to all crystals	7
3.4 Flatness.....	7
3.5 Definitions of appearance defects	10
3.6 Other terms and definitions	11
Bibliography.....	14
Figure 1 – Example of site distribution for LTV measurement.....	7
Figure 2 – LTV value of each site.....	8
Figure 3 – Schematic diagram of Sori	9
Figure 4 – Wafer sketch and measurement points for TV5 determination	9
Figure 5 – Schematic diagram of TTV	10
Figure 6 – Schematic diagram of warp	10
Table 1 – Description of wafer orientations	12

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Technical specifications are subject to review within three years of publication to decide whether they can be transformed into International Standards.

IEC TS 61944-4-4, which is a technical specification, has been prepared by IEC technical committee 49: Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection.

This third edition of IEC 61994-4-4 cancels and replaces the second edition published in 2010. This edition constitutes a technical revision.

This edition includes the following significant technical changes with respect to the previous edition:

- a) the new terms and definitions given in IEC 62276:2016 have been taken into account;
- b) the general title has been changed according to the change in the title of TC 49 in 2009.
- c) the part title has been changed according to the title of IEC 62276:2016.

The text of this technical specification is based on the following documents:

Enquiry draft	Report on voting
49/1283/DTS	49/1287/RVC

Full information on the voting for the approval of this technical specification can be found in the report on voting indicated in the above table.

This document has been drafted in accordance with the ISO/IEC Directives, Part 2.

A list of all parts in the IEC 61994 series, published under the general title *Piezoelectric, dielectric and electrostatic devices and associated materials for frequency control, selection and detection – Glossary*, can be found on the IEC website.

Future standards in this series will carry the new general title as cited above. Titles of existing standards in this series will be updated at the time of the next edition.

The committee has decided that the contents of this document will remain unchanged until the stability date indicated on the IEC website under "<http://webstore.iec.ch>" in the data related to the specific document. At this date, the document will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

A bilingual version of this publication may be issued at a later date.

PIEZOELECTRIC, DIELECTRIC AND ELECTROSTATIC DEVICES AND ASSOCIATED MATERIALS FOR FREQUENCY CONTROL, SELECTION AND DETECTION – GLOSSARY –

Part 4-4: Piezoelectric materials – Single crystal wafers for surface acoustic wave (SAW) devices

1 Scope

This part of IEC 61994 gives the terms and definition for single crystal wafers for surface acoustic wave (SAW) devices representing the state of the art.

2 Normative references

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

There are no normative references in this document.

3 Terms and definitions

For the purposes of this document, the following terms and definitions apply.

ISO and IEC maintain terminological databases for use in standardization at the following addresses:

- IEC Electropedia: available at <http://www.electropedia.org/>
- ISO Online browsing platform: available at <http://www.iso.org/obp>

3.1 Single crystals for SAW wafer

3.1.1

as-grown synthetic quartz crystal

right-handed or left-handed single crystal quartz grown hydrothermally

[SOURCE: IEC 62276:2016, 3.1.1, modified – Notes 1 and 2 to entry have been removed.]

3.1.2

lanthanum gallium silicate

LGS

single crystals described by the chemical formula $\text{La}_3\text{Ga}_5\text{SiO}_{14}$, grown by Czochralski (crystal pulling from melt) or other growing methods

[SOURCE: IEC 62276:2016, 3.1.5]

3.1.3

lithium niobate

LN

single crystals approximately described by chemical formula LiNbO_3 , grown by Czochralski (crystal pulling from melt) or other growing methods

[SOURCE: IEC 62276:2016, 3.1.2]

3.1.4

lithium tantalate

LT

single crystals approximately described by chemical formula LiTaO_3 , grown by Czochralski (crystal pulling from melt) or other growing methods

[SOURCE: IEC 62276:2016, 3.1.3]

3.1.5

lithium tetraborate

LBO

single crystals described by the chemical formula $\text{Li}_2\text{B}_4\text{O}_7$, grown by Czochralski (crystal pulling from melt), vertical Bridgman, or other growing methods

[SOURCE: IEC 62276:2016, 3.1.4]

3.2 Terms and definitions related to LN and LT crystals

3.2.1

curie temperature

T_c

phase transition temperature between ferroelectric and paraelectric phases measured by differential thermal analysis (DTA) or dielectric measurement

[SOURCE: IEC 62276:2016, 3.2.1]

3.2.2

polarization process

electrical process used to establish a single domain crystal

[SOURCE: IEC 62276:2016, 3.2.3]

3.2.3

reduction process

REDOX reaction to increase conductivity to reduce the harmful effects of pyroelectricity

[SOURCE: IEC 62276:2016, 3.2.4]

3.2.4

reduced LN

LN treated with a reduction process

[SOURCE: IEC 62276:2016, 3.2.5, modified – Note 1 to entry has been removed.]

3.2.5

reduced LT

LT treated with a reduction process

[SOURCE: IEC 62276:2016, 3.2.6, modified – Note 1 to entry has been removed.]

3.2.6

single domain

ferroelectric crystal with uniform electrical polarization throughout (for LN and LT)

[SOURCE: IEC 62276:2016, 3.2.2]

3.3 Terms and definitions related to all crystals

3.3.1

congruent composition

chemical composition of a single crystal in a thermodynamic equilibrium with a molten solution of the same composition during the growth process

[SOURCE: IEC 62276:2016, 3.3.2]

3.3.2

lattice constant

length of unit cell along a major crystallographic axis measured by X-ray using the Bond method

[SOURCE: IEC 62276:2016, 3.3.1]

3.3.3

twin

two or more same single crystals which are combined together by the law of symmetrical plane or axis

[SOURCE: IEC 62276:2016, 3.3.3, modified – Notes 1 and 2 to entry have been removed.]

3.4 Flatness

3.4.1

fixed quality area

FQA

central area of a wafer surface, defined by a nominal edge exclusion, X, over which the specified values of a parameter apply

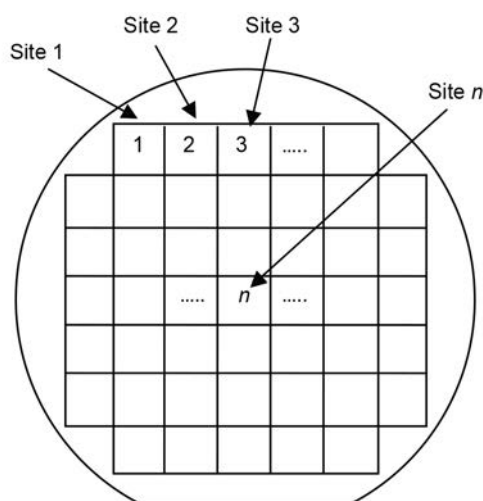
[SOURCE: IEC 62276:2016, 3.4.1, modified – Note 1 to entry has been removed.]

3.4.2

local thickness variation

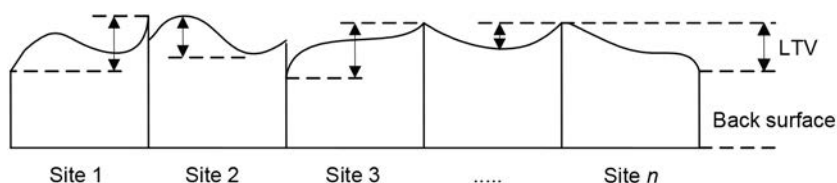
LTV

variation determined by a measurement of a matrix of sites with defined edge dimensions



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Figure 1 – Example of site distribution for LTV measurement



IEC

Figure 2 – LTV value of each site

Note 1 to entry: All sites have their centres within the FQA.

Note 2 to entry: Measurement is performed on a clamped wafer with the reference plane as defined in 3.4.5 a). A site map example is shown in Figure 1. The value is always a positive number and is defined for each site as the difference between the highest and lowest points within each site, as shown in Figure 2. For a wafer to meet an LTV specification, all sites shall have LTV values less than the specified value.

[SOURCE: IEC 62276:2016, 3.4.8]

3.4.3

focal plane deviation

FPD

deviation measured relative to the 3-point reference plane

Note 1 to entry: The 3-point reference plane is defined in 3.4.5 b).

Note 2 to entry: The value obtained indicates the maximum distance between a point on the wafer surface (within the FQA) and the focal plane. If that point is above the reference, the FPD is positive. If that point is below the reference plane, the FPD is negative.

[SOURCE: IEC 62276:2016, 3.4.10]

3.4.4

percent local thickness variation

PLTV

percentage of sites that fall within the specified values for LTV

Note 1 to entry: As with the LTV measurement, this is a clamped measurement.

[SOURCE: IEC 62276:2016, 3.4.9]

3.4.5

reference plane

plane depending on the flatness measurement and which can be any of the following:

- for clamped measurements, the flat chuck surface that contacts the back surface of the wafer;
- for without clamped measurements, three points at specified locations on the front surface within the FQA;
- for without clamped measurements, the least-squares fit to the front surface using all measured points within the FQA

[SOURCE: IEC 62276:2016, 3.4.2]

3.4.6

site

square area on the front surface of the wafer with one side parallel to the OF

Note 1 to entry: Flatness parameters are assessed either globally for the FQA, or for each site individually.

[SOURCE: IEC 62276:2016, 3.4.3]

3.4.7

Sori

maximum difference between a point on the front surface and a reference plane

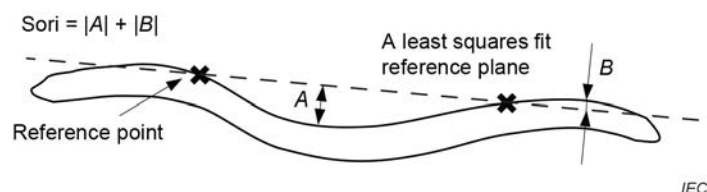


Figure 3 – Schematic diagram of Sori

Note 1 to entry: Sori describes the deformation of an unclamped wafer, as shown in Figure 3.

Note 2 to entry: In contrast to warp, in this case the reference plane is defined by a least-squares fit to the front surface (3.4.5 c)).

[SOURCE: IEC 62276:2016, 3.4.7]

3.4.8

thickness variation for five points

TV5

measure of wafer thickness variation defined as the maximum difference between five thickness measurements

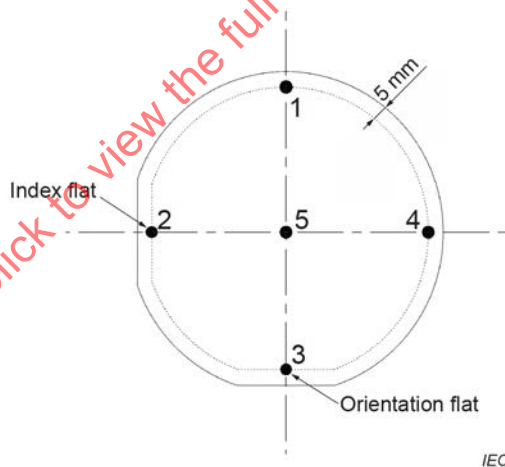


Figure 4 – Wafer sketch and measurement points for TV5 determination

Note 1 to entry: Thickness is measured at the centre of the wafer and at four peripheral points shown in Figure 4.

[SOURCE: IEC 62276:2016, 3.4.4]

3.4.9

total thickness variation

TTV

difference between the maximum thickness and the minimum thickness